

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI UHBS60-2 is Designed for

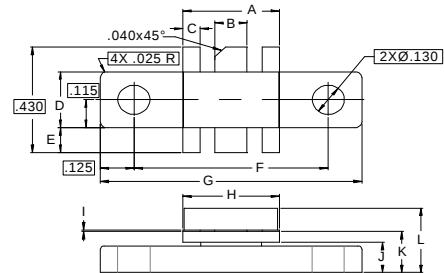
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CBO}	50 V
V_{CEO}	26 V
V_{CES}	50 V
V_{EBO}	4.0 V
P_{DISS}	190 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.9°C/W

PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

ORDER CODE: ASI10673

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 50\text{ mA}$	50			V
BV_{CES}	$I_C = 50\text{ mA}$	50			V
BV_{CEO}	$I_C = 50\text{ mA}$	26			V
BV_{EBO}	$I_E = 10\text{ mA}$	3.0			V
I_{CES}	$V_{CE} = 20\text{ V}$			10	mA
I_{CBO}	$V_{CB} = 30\text{ V}$			5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$	20		100	---
C_{ob}	$V_{CB} = 24\text{ V}$ $f = 1.0\text{ MHz}$			75	pF
P_G η_c	$V_{CE} = 24\text{ V}$ $P_{OUT} = 60\text{ W}$ $f = 960\text{ GHz}$	7.0	50		dB %